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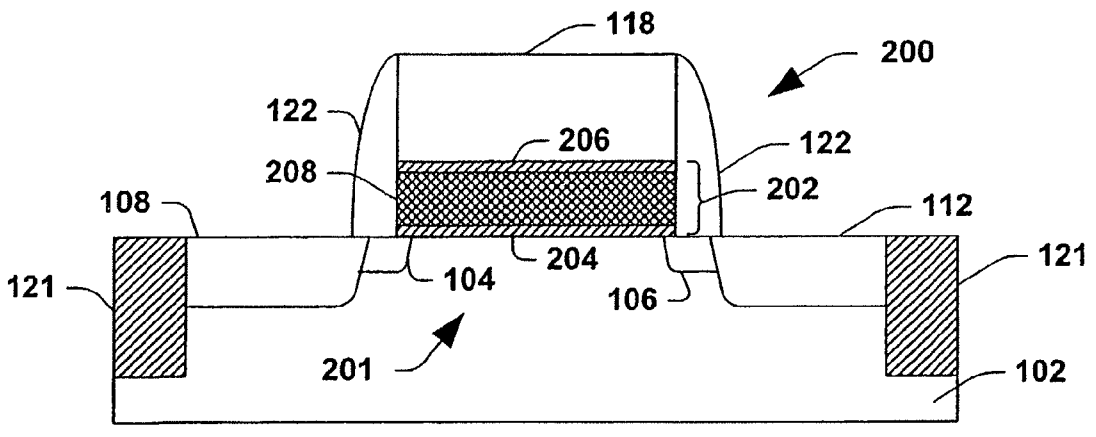
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(54) Title: GATE OXIDE PROCESS METHODS FOR HIGH PERFORMANCE MOS TRANSISTORS BY REDUCING REMOTE SCATTERING



(57) Abstract: The present invention relates to a MOS transistor structure (200, 210, 400) and method of manufacture (300, 500) which provides a high-k dielectric gate insulator (202, 402) for reduced gate current leakage while concurrently reducing remote scattering, thereby improving transistor carrier mobility.

WO 03/100835 A2